

DESCRIPTION

The MPQ8616 is fully integrated high frequency synchronous rectif ied step-down switch mode converter. It offers very compact solution sto achieve 6A/12A output current from a 3V to 6V input with excellent load and line regulation.

Constant-On-Time (COT) control mode provides fast transient respo nse and eases loop stabilization. The MPQ8616 can operate with a low-cost e lectrolytic capacitor and can support ceramic output capacitor with external slop е compensation.

Operating frequency is programmed by an external resistor and is compensated for variations in V_{IN}. It is almost constant with all the input voltage and output load conditions.

Under voltage lockout is internally set at 2.8 V, but can b e increa sed by prog ramming th e threshold with a resisto r network on the enable pin. The output voltage startup ramp is con trolled by the soft start pin. A power good sign al indicates the output is within its no minal voltage range.

Full fault pr otection including OCP, SCP, OVP UVP and OTP is provided by internal comparators.

The MPQ8 616 requires a min imum number of readily available standard external components and are available in QFN3x4 packages.

FEATURES

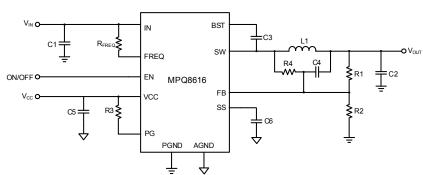
- Wide 3V to 6V Operating Input Range
- 6A/12A Output Current •
- Low R_{DS}(ON) Internal Power MOSFETs
- **Proprietary Switching Loss Reduction** Technique
- Adaptive COT for Ultrafast Transient Response
- 1% Reference Voltage Over -20°C to +85°C Junction Temperature Range
- Programmable Soft Start Time •
- Pre-Bias Start up
- Programmable Switching Freque ncy from 300kHz to 1MHz.
- Minimum On Time T_{ON MIN}=60ns Minimum Off Time TOFF MIN=100ns
- Non-latch OCP, non-l atch OVP Protection and Thermal Shutdown
- Output Adjustable from 0.61V to 4.5V

APPLICATIONS

- **Telecom System Base Stations**
- Systems Networking
- Server
- Personal Video Recorders •
- Flat Panel Television and Monitors
- Distributed Power Systems

All MPS parts are lead-free and adhere to the RoHS directive. For MPS green status, please visit MPS website under Products, Quality Assurance page. "MPS" and "The Future of Analog IC Technology" are registered trademarks of Monolithic Pover Systems, Inc.

TYPICAL APPLICATION

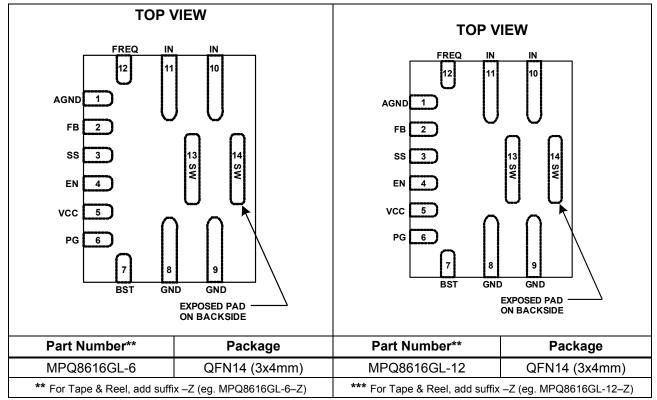




Part Number*	Package	Top Marking
	(2)(4mm)	MP8616
MPQ8616GL-6 QFN	6GL-6 QFN (3x4mm)	6
	(2)(4,00,00)	MP8616
MPQ8616GL-12 QFN	(3x4mm)	12

ORDERING INFORMATION

* For Tape & Reel, add suffix -Z (e.g. MPQ8616GL-6/12-Z);



PACKAGE REFERENCE

ABSOLUTE MAXIMUM RATINGS (1)

$ \begin{array}{llllllllllllllllllllllllllllllllllll$	Supply Voltage V _{IN}	5V
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	V _{SW} 0.3V to V _{IN} + 0.3	3V
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	V _{SW} (30ns)3V to V _{IN} + 3	3V
$\begin{array}{llllllllllllllllllllllllllllllllllll$		
All Other Pins0.3V to +6V Continuous Power Dissipation $(T_A=+25^\circ)^{(2)}$ QFN(3x4mm)2.6W Junction Temperature150°C Lead Temperature260°C	$V_{IN} - V_{SW}$ (30ns)3V to V_{IN} + 3	3V
Continuous Power Dissipation (T _A =+25°) ⁽²⁾ QFN(3x4mm)2.6W Junction Temperature150°C Lead Temperature260°C		
Continuous Power Dissipation (T _A =+25°) ⁽²⁾ QFN(3x4mm)2.6W Junction Temperature150°C Lead Temperature260°C	All Other Pins0.3V to +6	3V
Junction Temperature		
Lead Temperature260°C	QFN(3x4mm)2.6	W
•	Junction Temperature150°	°C
•	Lead Temperature	°C
	•	

Recommended Operating Conditions ⁽³⁾

Supply Voltage V _{IN}	
Output Voltage VOUT	0.61V to 4.5V
Operating Junction Temp. (T _J)	40°C to +125°C

Thermal Resistance $^{(4)}$ θ_{JA} θ_{JC}

QFN (3x4mm)...... 48..... 10... °C/W

Notes:

- 1) Exceeding these ratings may damage the device.
- 2) The maximum allowable power dissipation is a function of the maximum junction tempe rature T J(MAX), the junction-to-ambient thermal resistance θ_{JA}, and the ambient temperature T_A. The maximum allowable continuous power dissipation at any ambient temperature is calculated by P_D(MAX)=(T_J(MAX)-T_A)/θ_{JA}. Exceeding the maximum allowable power dissipation will cause excessive die temperature, and the regulator will go into thermal sh utdown. Inter rnal thermal shutdo wn circuitr y protects the device from permanent damage.
- 3) The device is not guarant eed to function outside of its operating conditions.
- 4) Measured on JESD51-7, 4-layer PCB.



ELECTRICAL CHARACTERISTICS

 V_{IN} = 5V, T_J = -40 to +125°C, unless otherwise noted.

Parameters Sy mbol Condition		Condition	Min	Тур	Max	Units	
Supply Current	·					·	
Supply Current (Shutdown)	I _{IN}	V _{EN} = 0V		1	2	μA	
Supply Current (Quiescent)	I _{IN}	V _{EN} = 2V, V _{FB} = 1V	0.6	1.05	1.3	mA	
MOSFET							
High-side Switch On Resistance	HS _{RDS-ON}	MPQ8616-6, T _J =25°C		19.8		mΩ	
	TORDS-ON	MPQ8616-12, T _J =25°C	16			11122	
Low-side Switch On Resistance	19	MPQ8616-6 T _J =25°C		15.3		m0	
Low-side Switch On Resistance	LS _{RDS-ON}	MPQ8616-12, T _J =25°C	8.4			mΩ	
Switch Leakage	SW _{LKG}	V_{EN} = 0V, V_{SW} = 0V or 5V		0.01	3	μA	
Current Limit			1		I		
High-side Current Limit	I	MPQ8616-6 9.5		12	14.5	Α	
	I _{LIMIT}	MPQ8616-12	17	23	27		
Timer			1		I		
One-Shot On Time	t _{on}	R_{FREQ} =165k Ω , V_{OUT} =1.2V		200		ns	
Minimum Off Time	t _{OFF}		50	100	150	ns	
Fold back Timer ⁽⁵⁾	t _{foldback}	OCP happens	2.5			μs	
Over-voltage and Under-voltage	Protection						
OVP Threshold	V _{OVP}		110% 1	20% 130	%	V	
OVP Delay ⁽⁵⁾	t _{OVP}			1		μs	
UVP Threshold ⁽⁵⁾	V _{UVP}		50%	0		V _{REF}	
Reference And Soft Start							
Reference Voltage	V _{REF}	$T_J = -20^{\circ}C$ to $+85^{\circ}C$	604	610	616	mV	
	V REF	$T_{J} = -40^{\circ}C$ to +125°C	601 610 619				
Feedback Current	I _{FB} V	_{FB} = 610mV		0.001	150	nA	
Soft Start Charging Current	I _{SS}	V _{SS} =0V 5		7.5	10	μA	



ELECTRICAL CHARACTERISTICS (continued)

 V_{IN} = 5V, T_J = -40 to +125°C, unless otherwise noted.

Parameters Sy	mbol	Condition	Min	Тур	Мах	Units		
Enable And UVLO								
Enable Input Low Voltage	VILEN		1.4		1.8	V		
Enable Hysteresis	V _{EN-HYS}			890		mV		
Enable Input Current	I	$V_{EN} = 2V$		1.5	2			
	I _{EN}	$V_{EN} = 0V$		0.01	1	μA		
VCC UVLO								
VCC Under Voltage Lockout Threshold Rising	VCC _{Vth}	2.3		2.8	2.95	V		
VCC Under Voltage Lockout Threshold Hysteresis	VCC _{HYS}			300		mV		
Power Good								
Power Good Rising Threshold	PG _{Vth-Hi}		84%	90%	96%	V_{REF}		
Power Good Falling Threshold	PG _{Vth-Lo}		63%	70%	73%	V _{REF}		
Power Good Deglitch Timer	PG_{Td}	T _{SS} =1ms,		2000	5000	μs		
Power Good Sink Current Capability	V _{PG} Sink	4mA			0.4	V		
Power Good Leakage Current	I _{PG_LEAK}	V _{PG} = 3.3V		50	150	nA		
Thermal Protection								
Thermal Shutdown	T _{SD} Note	5	150	160		°C		
Thermal Shutdown Hysteresis				25		°C		

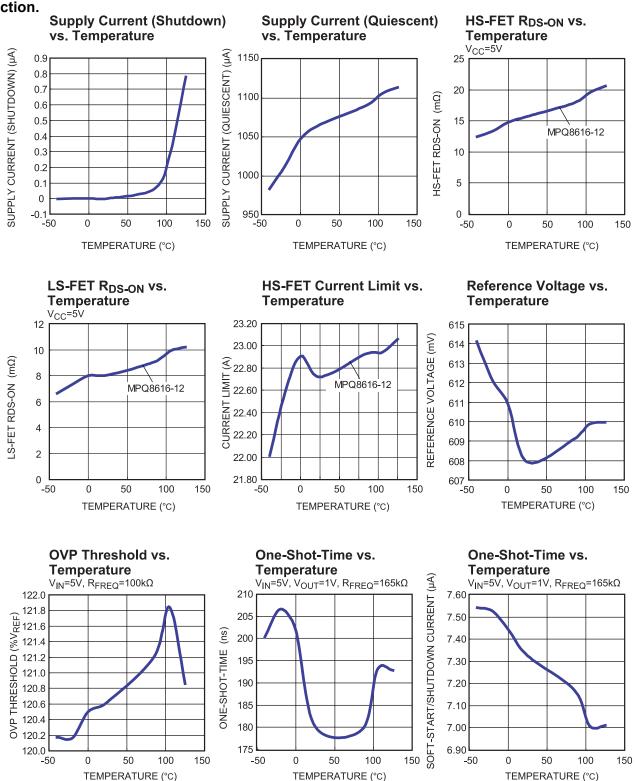
Note:

5) Guaranteed by design.

TYPICAL CHARACTERISTICS

EĘ

MPQ8616, Performance waveforms are tested on the evaluation board of the Design Example section.

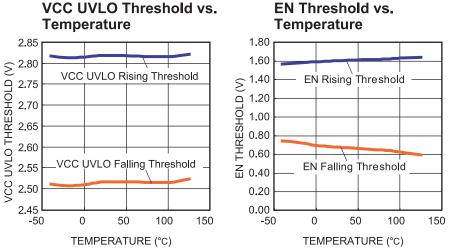




TYPICAL CHARACTERISTICS (continued)

▖▖▏ᡓᆚᠴ

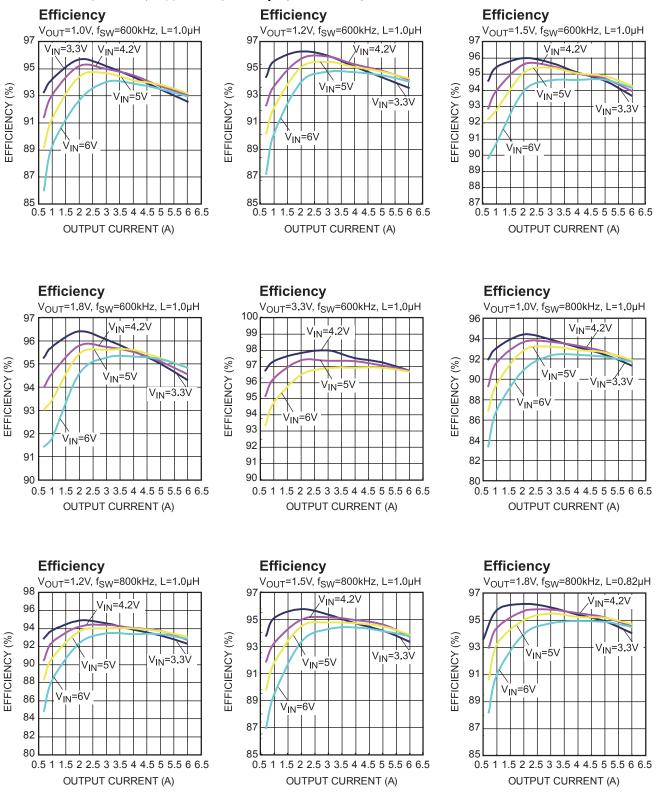
MPQ8616GL, Performance waveforms are tested on the evaluation board of the Design Example section.





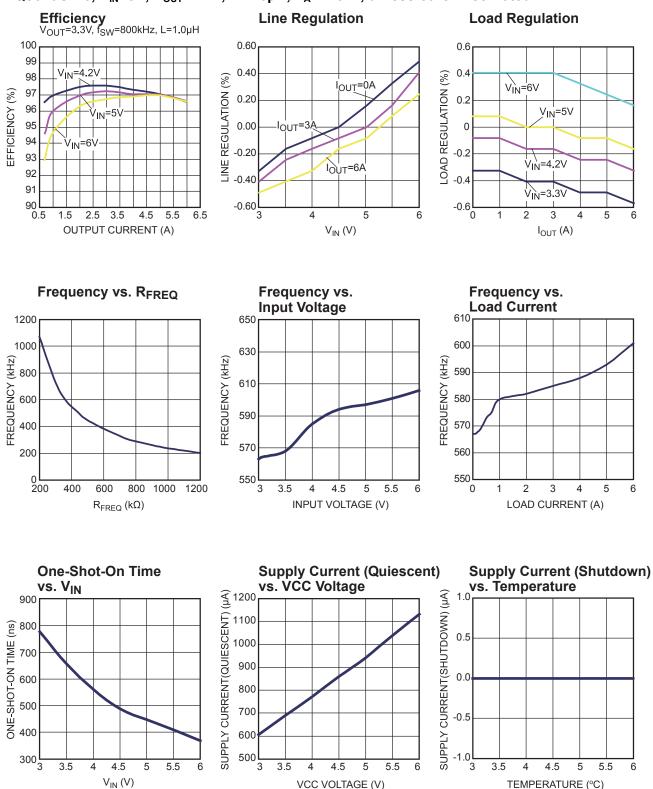
TYPICAL PERFORMANCE CHARACTERISTICS

Performance waveforms are tested on the evaluation board of the Design Example section. MPQ8616GL-6, V_{IN} =5V, V_{OUT} =1.2V, L=1.0µH, T_A =+25°C, unless otherwise noted.





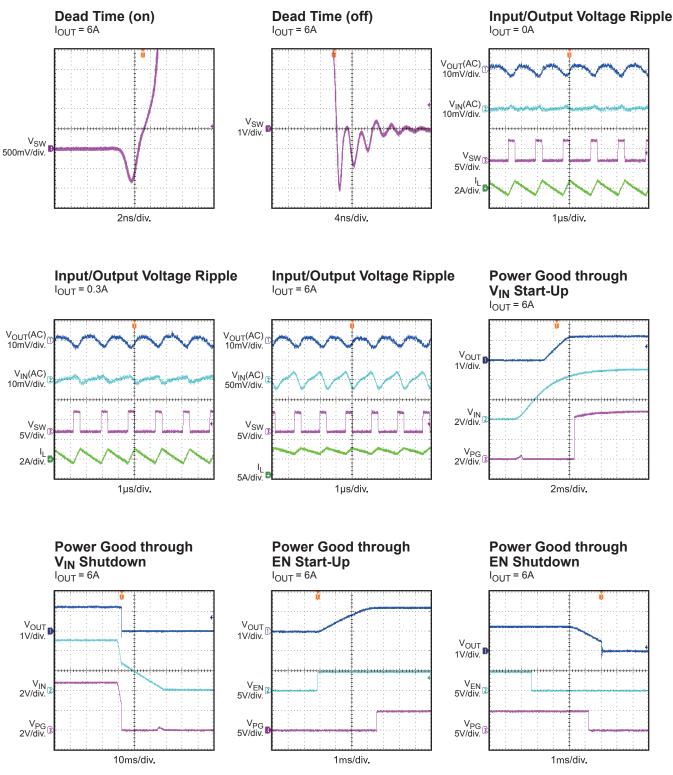
Performance waveforms are tested on the evaluation board of the Design Example section. MPQ8616GL-6, V_{IN} =5V, V_{OUT} =1.2V, L=1.0µH, T_A =+25°C, unless otherwise noted.



1.01 www.MonolithicPower.com MPS Proprietary Information. Patent Protected. Unauthorized Photocopy and Duplication Prohibited. © 2013 MPS. All Rights Reserved.

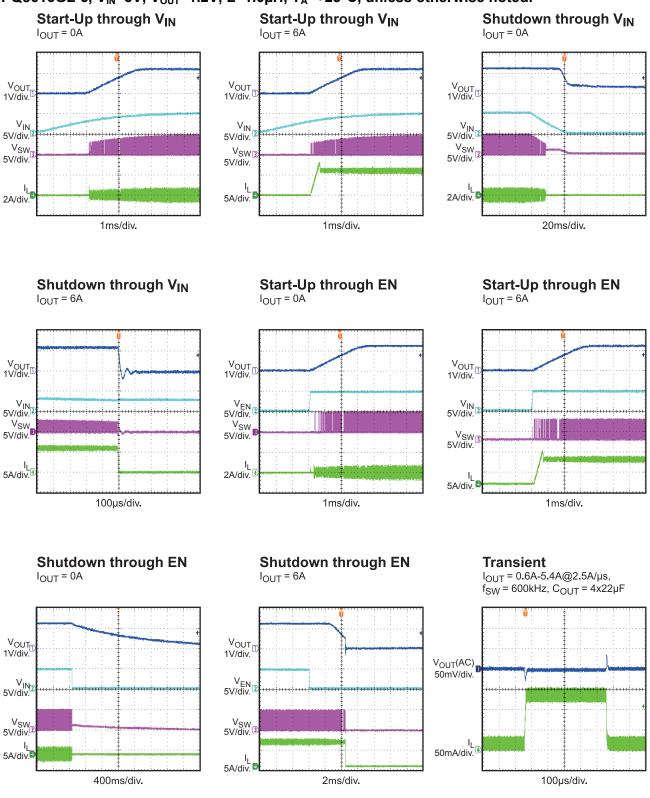


Performance waveforms are tested on the evaluation board of the Design Example section. MPQ8616GL-6, V_{IN} =5V, V_{OUT} =1.2V, L=1.0µH, T_A =+25°C, unless otherwise noted.





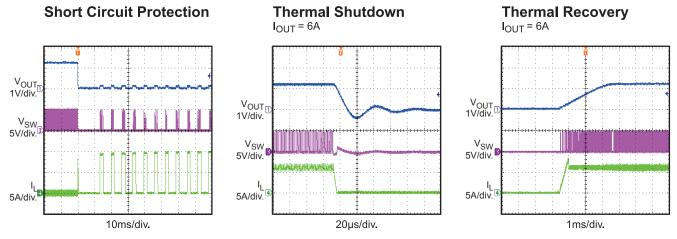
Performance waveforms are tested on the evaluation board of the Design Example section. MPQ8616GL-6, V_{IN} =5V, V_{OUT} =1.2V, L=1.0µH, T_A =+25°C, unless otherwise noted.



www.MonolithicPower.com MPS Proprietary Information. Patent Protected. Unauthorized Photocopy and Duplication Prohibited. © 2013 MPS. All Rights Reserved.



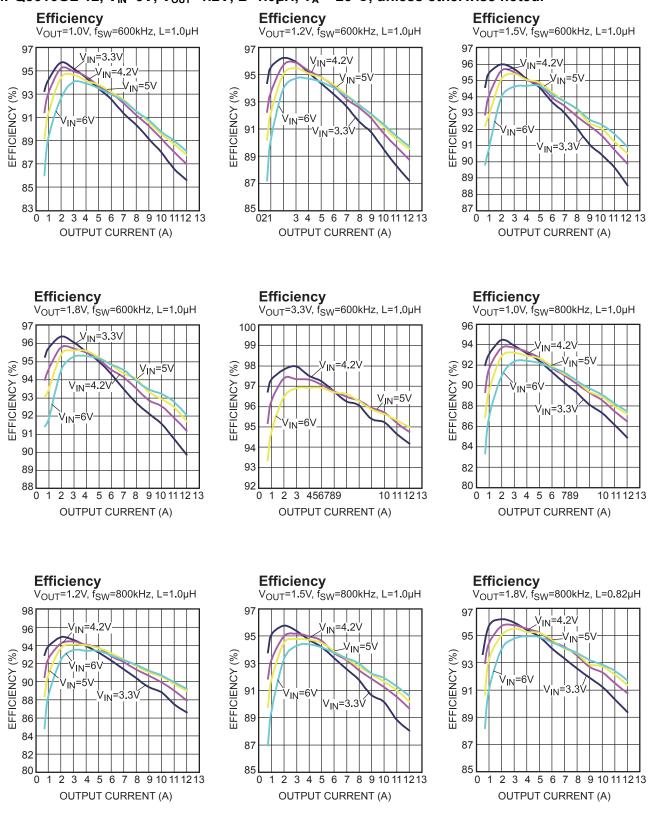
Performance waveforms are tested on the evaluation board of the Design Example section. MPQ8616GL-6, V_{IN} =5V, V_{OUT} =1.2V, L=1.0µH, T_A =+25°C, unless otherwise noted.





TYPICAL PERFORMANCE CHARACTERISTICS

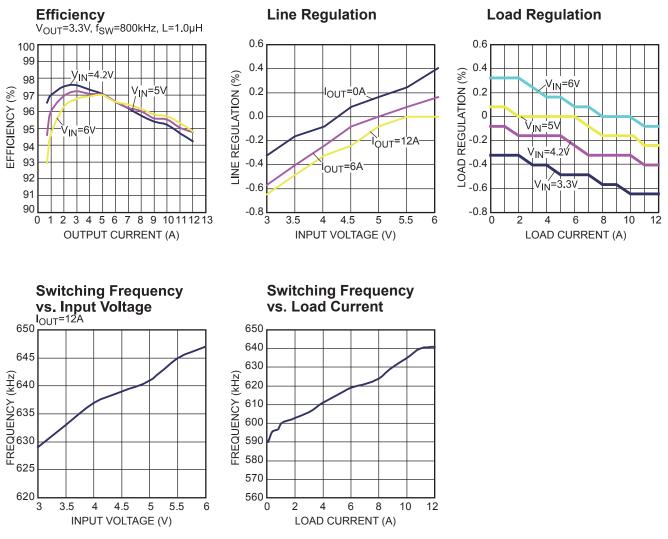
MPQ8616GL-12, V_{IN} =5V, V_{OUT} =1.2V, L=1.0µH, T_A =+25°C, unless otherwise noted.



www.MonolithicPower.com MPS Proprietary Information. Patent Protected. Unauthorized Photocopy and Duplication Prohibited. © 2013 MPS. All Rights Reserved.

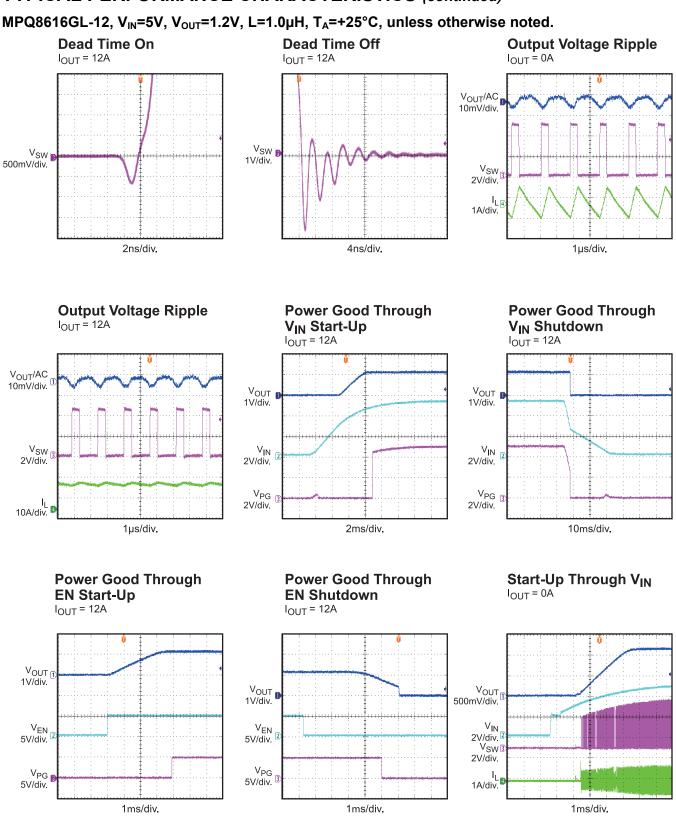


MPQ8616GL-12, V_{IN} =5V, V_{OUT} =1.2V, L=1.0µH, T_A =+25°C, unless otherwise noted.









www.MonolithicPower.com MPS Proprietary Information. Patent Protected. Unauthorized Photocopy and Duplication Prohibited. © 2013 MPS. All Rights Reserved.



լլ

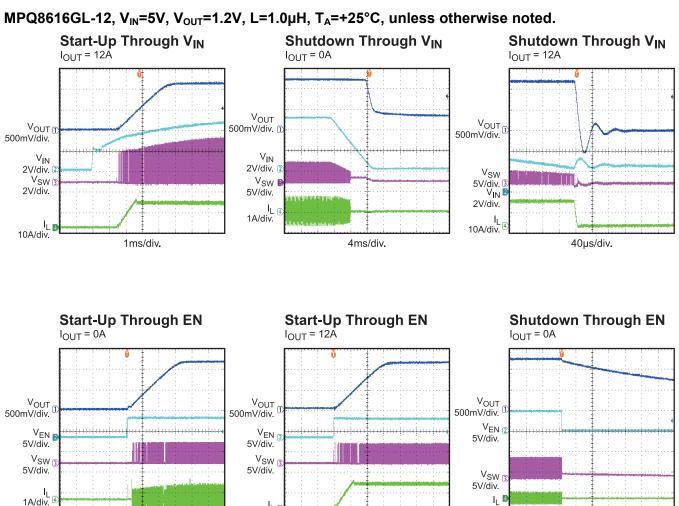
400ms/div.

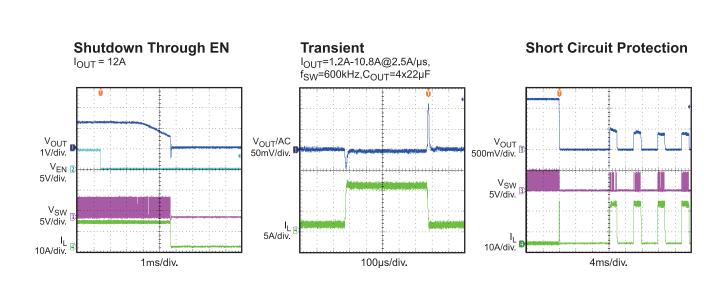
2.5A/div.

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

ا 1A/div.

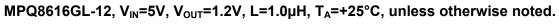
1ms/div.

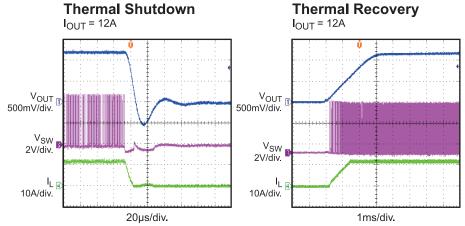




1ms/div.







mps:

PIN FUNCTIONS

MPQ8616GL-6, MPQ8616GL-12

PIN #	Name	Description
1	AGND	Analog ground.
2 FB		Feedback. An external resistor divider from the output to GND, tapped to the FB pin, sets the output voltage. It is recommended to place the resistor divider as close to FB pin as possible. Vias should be avoided on the FB traces.
3 SS		Soft Start. C onnect on ex ternal capacitor to pro gram the soft start time for the switch mode regulator.
4 EN		Enable pin. Pull this pin higher than 1.8V to enable the chip. For automatic start-up, connect EN pin to VIN with 100K Ω resistor. Can be used to set the on/off threshold (adjust UVLO) with two additional resistors.
5 VCC		Supply Voltage for driver and control circuits. Decouple with a minimum 4.7μ F ceramic capacitor as close to the pin as possible. X7R or X5R grade dielectric ceramic capacitors are recommended for their stable temperature characteristics.
6 PG		Power good output. It is high if the o utput voltage is higher th an 90% of the nominal voltage. There is a delay from FB \ge 90% to PG goes high.
7 BST		Bootstrap. A capacitor connected between SW and BS pins is required to form a floating supply across the high-side switch driver.
8-9 GNI	כ	System Ground. This pin is the reference ground of the regulated output voltage. For this reason care must be taken in PCB layout.
10-11 IN		Supply Voltage. The IN pin supplies power for int ernal MOSF ET and regulator. The MPQ8616 operate from a +3V to +6V input rail. An input capacitor is needed to decouple the input rail. Use wide PCB traces and multiple vias to make the connection.
12	FREQ	Frequency setting pin. A resistor connected between FREQ and IN is required to set the switching frequency. The ON time is determined by the input voltage and the resistor connected to the FREQ pin. IN connect through a resistor is used for line feed-forward and makes the frequency basically constant during input voltage's variation. An optional 1nF decoupling capacitor can be added to improve any switching frequency jitter that may be present.
13-14 SV	V	Switch Output. Connect this pin to the inductor and bootstrap capacitor. This pin is driven up to the VIN voltage by the high -side switch during the on-time of the PWM duty cycle. The inductor current drives the SW pin negative during the off-time. The on-resistance of the low-side switch and the internal Schottky diode fixes the nega tive voltage. Use wide PCB traces to make the connection.



BLOCK DIAGRAM

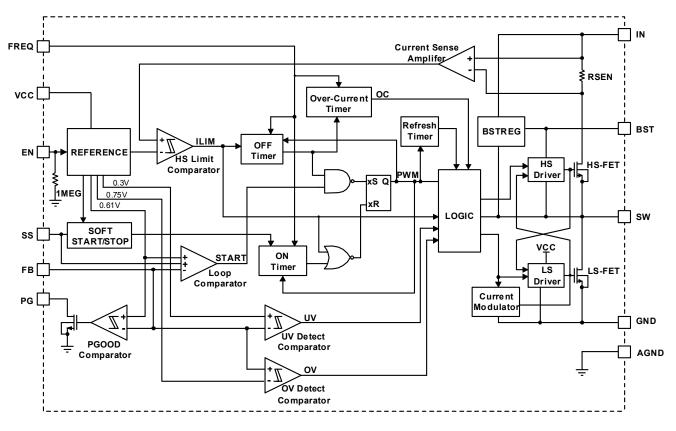


Figure 1—Functional Block Diagram



OPERATION

PWM Operation

The MPQ8616 is fully integrated synchronous rectified step-down switch mode converter. Constant-on-time (COT) control is employed to provide fast transient response and easy loop stabilization. At the beginning of each cycle, the high-side MOSFET (HS-FET) is turned ON when the feedback voltage (V_{FB}) is below the reference voltage (V_{REF}), which indicates insufficient output voltage. The ON period is determined by the input voltage and the frequency-set resistor as follows:

$$t_{ON} ns) = \frac{4.8 \times \mathbf{R}_{FREQ}(k)}{V_{IN}(V) - 0.49}$$
 (1)

After the ON period elapses, the HS-FET is turned off, or becomes OFF state. It is turned ON again when V _{FB} drops below V _{RFF}. By repeating operation this way, the converter r equlates the output voltage. The integrated low-side MOSFET (LS-FET) is turned on when the HS-FET is in it s OFF state to minimize the conduction loss. The re will be a de ad short be tween input and GND i f both HS-FET and LS-FET are turned on at th е same time. It's called shoot-through. In order to avoid shoot-through, a dead-time (DT) is internally generated between HS-FET off and LS-FET on, or LS-FET off and HS-FET on.

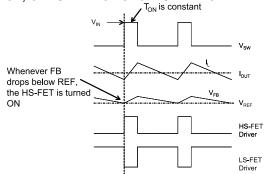


Figure 2—PWM Operation

MPQ8616 always op erating in continuou sconduction-mode (CCM), which means the inductor cur rent can go negative at light load. The CCM mode operation is sho wn in Figure2. When V_{FB} is below V_{REF}, HS-MOSFET is turn ed on for a fixed interval which is de termined by one- shot on-timer as equation 1 shown. When

the HS-MOSFET is tur ned off, th e LS-MOSFET is turned on until next period.

For the MPQ8616 is operated in CCM, t he switching fr equency is fairly constant and it is called PWM mode.

Switching Frequency

The selection of switching frequency is a trade off between efficiency an d component size. Lo w frequency operation increases e fficiency b v reducing MOSFET switching losses, but requires larger inductance and capacitan ce to maintai n low output voltage ripple.

For MPQ86 16, the on time can be set usin g FREQ pin, then the fre quency is set in steady state operation at CCM mode.

Adaptive constant-on-time (COT) control is u sed in MPQ8616 and there is no dedicated oscillat or in the IC. Connect FREQ pin to IN pin t hrough resistor R FREQ and the input volt age is fee dforwarded to the one-shot on-time timer through the resisto r R FREQ. When in steady state operation a t CCM, th e duty ratio is kept as V_{OUT}/V_{IN} . Hence the switching frequency is fairly constant o ver the input voltage range. The switching frequency can be set as follows:

$$f_{SW}(kHz) = \frac{10^{6}}{\frac{4.8 \times R_{FREQ}(k\Omega)}{V_{IN}(V) - 0.49} \times \frac{V_{IN}(V)}{V_{OUT}(V)} t_{DELAY} ns)}$$
(2)

Where t_{DELAY} is the comparator delay. It's about 40ns.

Generally, the MPQ86 16 is set for 300kHz to 1MHz application. It is optimized to operate at high switch ing frequen cy with high efficien cy. High switch ing frequen cy makes it possib le t o utilize small sized LC fi Iter components to save system PCB space.

Jitter and FB Ramp Slope

Figure 3 shows jitter occurring in PWM mode. When there is noise in the V_{FB} downward slope, the ON time of HS-FET deviates from its intended lo cation and produces jitter. It is necessary to understand that there is a relationship between a system's sta bility and the steepness of the V _{FB} ripple's dow nward slope. The slope steepness of the V_{FB} ripple dominates in noise immunity. The magnitude of the $$V_{\mbox{\scriptsize FB}}$$ ripple doe sn't affe ct the noise immunity directly.

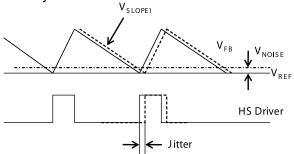


Figure 3—Jitter in PWM Mode

Ramp with Large ESR Capacitor

In the case of POSCAP or other types of capacitor with lager ESR is applied as output capacitor, the ESR ripple dominates the output ripple, and the slope on the FB is quite ESR related. Figure 4 shows an equivalent circuit in PWM mode with the HS-FET off and without an external ramp circuit. Turn to application information section for design steps with large ESR capacitors.

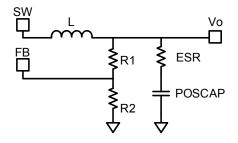


Figure 4—Simplified Circuit in PWM Mode without External Ramp Compensation

To realize the stability when no external ramp is applied, usually the ESR value should be chosen as follow:

$$R_{ESR} \ge \frac{\frac{t_{SW}}{0.7 \times \pi} + \frac{ON}{2}}{C_{OUT}}$$
(3)

 T_{SW} is the switching period.

Ramp with Small ESR Capacitor

When the output capa citors are ceramic ones, the ESR ripple is not high enough to stabilize the system, an d external ramp compensation is needed. Skip to application information section for design steps with small ESR caps.

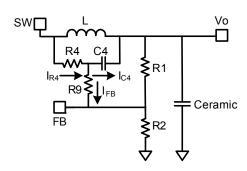


Figure 5—Simplified Circuit in PWM Mode with External Ramp Compensation

In PWM mode, an equivalent circuit with HS-FET off and the use of an external ramp compensation circuit (R4, C4) is simplified in Figure 5. The external ramp is derived from the inductor rip ple current. If one chooses C4, R9, R1 and R2 to meet the following condition:

$$\frac{1}{2f_{t \times SW} \times C_4} < \frac{1}{20} \left(\frac{R_1 \times R_2}{R_1 + R_2} + R_9 \right)$$
(4)

Where:

$$I_{R_4} = {}_{C_4} + I_{FB} \approx I_{C_4}$$
 (5)

And the ramp on the $V_{\mbox{\scriptsize FB}}$ can then be estimated as:

$$V_{\text{RAMP}}^{\dagger} = \times \frac{V_{\text{IN}} - V_{\text{O}}}{R_{\text{C}} \times \frac{1}{4}} \quad \text{on} \times \left(\frac{R_1 //R_2}{R_1 //R_2 + R_9}\right) \quad \textbf{(6)}$$

The downward slope of the V $_{\mbox{\scriptsize FB}}$ ri pple t hen follows:

$$V_{\text{SLOPE1}} \stackrel{V_{\text{RAMP}}}{== t_{\text{RAMP}}} \quad \frac{-V_{\text{OUT}}}{\frac{4}{4} \times C_4}$$
(7)

As can be seen from equation 7, if there is instability in PWM mod e, we can reduce eith er R4 or C4. If C4 can not be reduced further due to limitation fr om equation 4, then we can only reduce R4. For a stable PWM o peration, th e V_{slope1} should be design follow equation 8.

$$-\underbrace{\underbrace{t_{sw}}_{OPE1}}_{2\underline{k}} \times \underbrace{\frac{t_{oN}}{0.7 \times \pi} + \frac{t_{oN}}{2} - R_{ESR} \times C_{OUT}}_{2\underline{k}} \times \underbrace{C_{OUT}}_{OUT}}_{UT} \times \underbrace{t_{oN}}_{UT} + \frac{0.7 \times \underbrace{t_{oN}}_{0} - 10^{-3}}{t_{sw} - t_{on}}}_{t_{oN}}$$
(8)

Where Io is the load current.





Soft Start/Stop

The MPQ8 616 employs soft start/stop (S S) mechanism to ensure smooth o utput during power up and power down.

When the EN pin be comes high, an internal current source (8μ A) charges up the SS capacitor C6. The SS capacitor voltage takes over the REF voltage to the PWM comparator. The outp ut voltage smoothly ramps up with the SS voltage. Once the SS voltage reaches the same level a s the REF voltage, it keeps ramping up while V_{REF} takes over the PWM comparator. At this point, the soft start finishes a nd it enters into steady state operation.

When the EN pin is pulled to low, the SS CAP voltage is discharged through an 8uA internal current source. Once the SS voltage reaches REF voltage, it takes over the PWM comparator. The output voltage will decrease smoothly with SS voltage until zero level. The SS capacitor value can be determined as follows:

$$C(s_{s} nF) = \frac{t_{ss}(ms) \times \mu_{ss}(A)}{V_{REF}}$$
(9)

If the out put capacitors have large capacitance value, it's n ot recommended to set the SS time too small. Otherwise, it's easy to hit the current limit during SS. A minimum value of 4.7nF should be used if the output capacitance value is larger than 330μ F.

Pre-Bias Startup

If the output is pre-bia sed to a certain voltage during start up, the MPQ8616 will disable e the switching of both high-side and low-side switches until the voltage on the inter nal soft-st art capacitor exceeds the sensed output voltage a t the FB pin.

Power Good (PG)

The MPQ8 616 has po wer-good (PG) output. It can be connected to V_{CC} or other voltage source through a resistor (e.g. 100k). When the MPQ8616 is powered on and FB voltage reaches

above 90% of REF voltage, the PG pin is pulled high.

When the FB voltage drops to 70% of REF voltage or the part is not powered on, the PG pin will be pulled low.

Over-Current Protection (OCP)

The MPQ8 616 enters over-current protectio n mode when the induct or current hit s the current t limit, and tries to recover from o ver-current fault with hiccup mode. Th at means in over-current protection, the chip will disa ble o utput power stage, discharge soft- start capa citor and the n automatically try to soft -start again. If the overcurrent con dition still h olds after soft-start end s, the chip re peats this operation cycle till ove rcurrent disappears and output rises back t o regulation level. The MPQ8616 also operates in hiccup mode when short circuit happens.

Over/Under – Voltage Protection (OVP/UVP)

The MPQ8 616 has n on-latching over voltage protection. It monitors the output voltage through a resistor divider feedback (FB) voltage to detect over-voltage on the output. When the FB voltage e is higher than 120% of the REF voltage (0.610V), the LS-FET will be turned on while the HS-FET will be off. The LS-FET keeps on u ntil it hit s the negative current limit and turns off for 100ns. If over voltage condition still holds, the chip repeats this operati on cycle till the FB voltage drops below 110% of the REF voltage.

When the FB voltage is below 50% of the REF voltage (0.610V), it is recognized as und ervoltage (UV). Usually, UVP accompanies a hit in current limit and results in OCP.

Configuring the EN Control

The EN pin provides electrical on /off control of the device. Set EN high to turn on t he regulator and low to turn it off. Do not float this pin.

For automatic start-up, the EN pin can be pulle d up to in put voltage thr ough a re sistive voltage divider. Choose the values of the pull-up resist or $(R_{UP} \text{ from VIN pin to EN pin})$ and the pull-dow n resistor $(R_{DOWN} \text{ from EN pin to GND})$ t o determine the automatic start-up voltage:

$$V_{\text{IN-START}} = 4.4 \quad \frac{R_{B} + D_{\text{DOWN}}}{R_{\text{DOWN}}}$$
(10)

For example, for R $_{UP}$ =100k Ω and R $_{DOWN}$ =51k Ω , the V_{IN-START} is set at 4.15V.

To avoid noise, a 10n F ceramic capacitor from EN to GND is recommended.

There is a n internal zener diode o n the EN pin, which clam ps the EN pin voltage to prevent it from running away. The maximum pull up current assuming a worst case 6V internal zener clamp should be less than 1mA. Therefore, when EN is driven by an external logic signal, the EN voltage should be lower than 6V; when EN i s connected with VIN through a pu II-up resistor or a resistiv e voltage divider, the resistance se lection should ensure the maximum p ull up current less tha n 1mA.

If using a resistive voltage divider and VIN higher than 6V, the allowed minimum pull-up resistor R_{UP} should meet the following equation:

$$\frac{V_{\text{I}_{N}}(V) - 6}{R_{\text{UP}}(k\Omega\Omega} - \frac{6}{R_{\text{DOWN}}(k)} \quad 1(\text{mA}) \quad (11)$$

As a result, when just the pull-up resistor R $_{UP}$ is applied, the $V_{IN-START}$ is determined by i nput UVLO. The value of R_{UP} can be got as:

$$R_{\text{MP}}(k\Omega) > \frac{V_{\text{IN}}(V) - 6}{1(mA)}$$
(12)

A typical pull-up resistor is $100k\Omega$.

UVLO protection

The MPQ8616 has under-voltage lock-out protection (UVLO). Wh en the VCC voltage is higher than the UVLO rising thre shold voltag e, the MPQ8616 will be powered up. It shut s o ff when the VCC voltage is lower tha n the UVLO falling thre shold volta ge. This is non-latch protection. The MPQ8616 is disabled when the VCC voltage falls below its UVLO fal ling threshold (2.45V). If an application requires a higher under-voltage lockout (UV LO), use the e EN pin a s shown in Figure 6 to adjust the input volta ge UVLO b y using two e xternal resistors. It is re commended to use the enable re sistors to set the UVLO falling threshold (V $_{\text{STOP}}$) above 2.8 V. The risin g threshold (V_{START}) should be set to provide enough hysteresis to allow for any input supply variations.

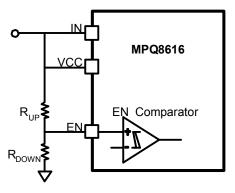


Figure 6—Adjustable UVLO

Thermal Shutdown

Thermal shutdown is employed in the MPQ8616. The junction temperature of the I C is internally monitored. If the junction tempera ture exceeds the thresh old value (minimum 150°C), the converter shuts off. This is a non-latch protection. There is about 25°C hysteres is. Once the junction temperature drops to a bout 125°C, it initiates a soft startup.



APPLICATION INFORMATION

Setting the Output Voltage-Large ESR Caps

For applications that electrolytic capacitor or POS capacitor with a controlled output o f ESR is set as output capacitors. The output voltage is set by feedback resistors R1 and R2. As figure 7 shows.

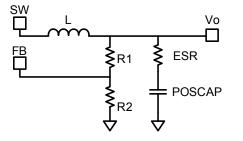


Figure7—Simplified Circuit of POS Capacitor

First, choo se a value for R2. R2 should be chosen rea sonably, a small R2 will lead to considerable quiescent current lo ss while to o large R2 makes the FB noise sensitive. It is recommended to choo se a value within 5k Ω -100k Ω for R2, using a comparatively larger R2 when V_{OUT} is low, and a smaller R2 when V_{OUT} is high. Then R1 is determined as follow with the output ripple considered:

$$RR = \frac{V_{OUT} - \frac{1}{2} \times \Delta V_{OUT} - V_{REF}}{V_{REF}}$$
 (13)

 $\Delta V_{\mbox{\scriptsize OUT}}$ is the output ripple determined by equation 21.

Setting the Output Voltage-Small ESR Caps

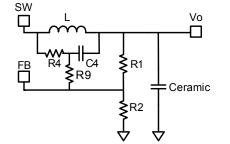


Figure8—Simplified Circuit of Ceramic Capacitor

When low ESR ceramic capacitor is used in the output, an external voltage ramp should be added to FB through resistor R4 and capacit or C4. The output voltage is influen ced by ramp voltage V_{RAMP} besides resistor divider as shown

in Figure 8 . The V $_{\text{RAMP}}$ can be calculated a s shown in equation 6. R2 should be chosen reasonably, a small R2 will lead to considerable quiescent current loss while too large R2 makes the FB noise sensitive . It is recommended t o choose a value within 5k Ω -100k Ω for R2, using a comparatively larger R2 when V $_{\text{OUT}}$ is low, and a smaller R2 when V $_{\text{OUT}}$ is high. And the value of R1 then is determined as follow:

$$R_{1} = \frac{R_{2}}{\frac{V_{FB(AVG)}}{V_{OUT} - V_{FB(AVG)}} - \frac{R_{2}}{R_{4} - R_{9}}}$$
(14)

The V $_{FB(AVG)}$ is the average value on the F B. V_{FB(AVG)} varies with t he Vin, Vo, and load condition, etc.. It is means the load regulation is strictly related to the V $_{FB(AVG)}$. Also the line regulation is related to the V $_{FB(AVG)}$, if one wants to gets a better load or line regulation, a lower V_{RAMP} is suggested once it meets equation 8.

For PWM operation, V $_{FB(AVG)}$ value can be deduced from equation 15.

$$V_{\text{FB}(\text{AVG})} = V_{\text{REF}} + \frac{1}{2R} \times V_{\text{RAMP}} \times \frac{R_1 / / R_2}{\frac{1}{R_2 + R_9}} \quad \text{(15)}$$

Usually, R9 is set to 0 Ω , and it can also be set following equation 16 for a better no ise immunity. It should b e set to b e 5 timers smaller than R1//R2 to minimize its influence on Vramp.

$$R_9 \leq \frac{1}{10} \frac{R_1 \times R_2}{R_1 + R_2}$$
 (16)

Using equation 14 and 15 to calculate the output voltage can be complicated. T o simplify the calculation of R1 in equation 14, a DC-blocking capacitor Cdc can be added to filter the DC influence fr om R4 and R9. Figur e 9 shows a simplified circuit with external ramp compensation and a D C-blocking capacitor. With this capacit or, R1 can easily be obtained by using equation 17 for PWM mode operation.

$$RR = \frac{V_{OUT} - V_{REF}}{V_{REF} + \frac{1}{2} \times V_{RAMP}} \times (17)$$

Cdc is sugg ested to be at least 10 times larger than C4 for better DC blocking performance, and should be not larger than 0.47μ F considering startup performance. In case one wants to use larger Cdc for a better FB noise immunity,

MPS.

combined with reduced R1 and R2 to limit the Cdc in a reasonable value without affecting the system start up. Be noted that even when the Cdc is applied, the load and line regulation are still Vramp related.

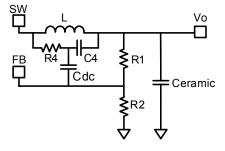


Figure9—Simplified Circuit of Ceramic Capacitor with DC blocking capacitor

Input Capacitor

The input current to the step-down converter is discontinuous. Therefore, a capacit or is require d to supply t he AC current to the step-down converter while maintaining the DC input voltage. Ceramic ca pacitors are recommen ded for best performance. In the layout, it's recommended to put the input capacitors as close to the IN pin as possible.

The capa citance varies significantly over temperature. Capacitors with X5R and X7R ceramic die lectrics are recommen ded because they are fairly stable over temperature.

The capacit ors must also have a ripple current rating great er than the maxi mum input ripple current of th e converter. The input r ipple current can be estimated as follows:

$$I_{EIN} = \times_{OUT} \sqrt{\frac{V_{OUT}}{V_{IN}} \times (1 - \frac{V_{OUT}}{V_{IN}})}$$
(18)

The worst-case conditio n occurs at $V_{IN} = 2V_{OUT}$, where:

$$I_{CIN} = \frac{I_{OUT}}{2}$$
(19)

For simplification, cho ose the in put capacit or whose RMS current rating is greate r than half of the maximum load current.

The input capacitance value determines the input voltage ripple of the converter. If there is input voltage ripple requirement in the system design, choose the input capacitor that meets th e specification The input voltage ripp le can be estimated a s follows:

$$\Delta \Psi_{IN} = \frac{I_{OUT}}{f Q_{V} \times I_{IN}} \times \frac{V_{OUT}}{V_{IN}} \times 1 - \frac{V_{OUT}}{V_{IN}})$$
(20)

The worst-case condition occurs at VIN = 2VOUT, where:

$$\Delta \Psi_{IN} = \frac{1}{4} \times \frac{I_{OUT}}{f_{SW} \times C_{IN}}$$
(21)

Output Capacitor

The output capacitor is required to maintain the DC output voltage. Ceramic or POSCAP capacitors are recommended. The output voltage ripple can be estimated as:

$$\Delta \Psi_{\text{OUT}} - \frac{V_{\text{OUT}}}{fJ_{\text{W}} \times \times} \times 1 - \frac{V_{\text{OUT}}}{V_{\text{IN}}}) \times (R_{\text{ESR}} + \frac{1}{8 - f_{\text{SW}} \times C_{\text{OUT}}})$$
(22)

In the case of ceramic capacitors, the impedance at the switching frequency is dominated by the capacitance. The output voltage ripple is mainly caused by the capacit ance. For simplificat ion, the output voltage ripple can be estimated as:

$$\Delta \forall \mathcal{L}_{\text{UT}} = \frac{V \mathcal{L}_{\text{UT}}}{8f \times_{\text{SW}}^{2} L \times C_{\text{OUT}}} \times 1 - \frac{OUT}{V_{\text{IN}}})$$
(23)

The output voltage ripple caused by ESR is very small. Therefore, an external ramp is needed t o stabilize the system. The external ramp can be generated through resistor R4 and capacitor C4 following equation 4, 7 and 8.

In the case of POSCAP capacitor s, the ESR dominates the impedance at the switching frequency. The ramp voltage gene rated from the ESR is hig h enough t o stabilize the system. Therefore, an external ramp is n ot needed. A minimum ESR value a ccording to equation 3 is required to ensure st able opera tion of the converter. For simplification, the output ripple can be approximated as:

$$\Delta \Psi_{\text{out}} = \frac{V_{\text{out}}}{f J_{\text{W}} \times} \times (1 - \frac{V_{\text{out}}}{V_{\text{IN}}}) \times R_{\text{ESR}}$$
(24)

Inductor

The induct or is required to supply constant current to the output load while being driven by the switch ing input voltage. A larger value inductor will result in less ripple current and lower output ripple voltage. However, a larger value

www.MonolithicPower.com MPS Proprietary Information. Patent Protected. Unauthorized Photocopy and Duplication Prohibited. © 2013 MPS. All Rights Reserved.



inductor will have a larger physical size, higher series resistance, and/or lower saturation current. A good rule for determining the inductor value is to allow the peak-to-peak ripple current in the inductor to be approximately 10~30% of the maximum output current. Also, make sure that the peak inductor current is below the current limit of the device. The inductance value can be calculated as:

$$L(=\times \frac{V_{OUT}}{fl_{W} \times \Delta_{L}} \quad 1 - \frac{V_{OUT}}{V_{IN}})$$
(25)

Where ΔI_L is the peak-to-peak inductor ripple current.

Choose an inductor tha t will not sa turate under the maxi mum inductor peak curren t. The peak inductor current can be calculated as:

$$I_{LP} = I_{OUT} \quad \frac{V_{OUT}}{2f \times_{SW} L} \times (1 - \frac{V_{OUT}}{V_{IN}})$$
(26)

The induct ors listed in Table 1 are highly recommended for the high efficie ncy they can provide.

Table 1—Inductor Selection Guide	e
----------------------------------	---

Part Number	Manufacturer	Inductance (µH)	DCR (mΩ)	Current Rating (A)	Dimensions L x W x H (mm ³)	Switching Frequency (kHz)
FDU1250C-R50M T	ОКО	0.50	1.3	46.3	13.3 x 12.1 x5	1000
FDU1250C-R56M T	DKO	0.56	1.6	42.6	13.3 x 12.1 x5	800-1000
FDU1250C-R75M T	рко	0.75	1.7	32.7	13.3 x 12.1 x5	600-800
FDU1250C-1R0M	TOKO	1.0	2.2	31.3	13.3 x 12.1 x5	600

Typical Design Parameter Tables

The following tables include r ecommended component values for typical ou tput voltages (1.0V, 1.2V, 1.8V, 3.3V) and switching frequencies (600kHz, 800kHz, and 1MHz). Refer to Tables 2 -4 for desig n cases wit hout external ramp comp ensation and Tables 5- 6 for desig n cases wit h external ramp compensation. External ra mp is not needed when high-ESR capacitors, such as electrolytic or POSCAPs are used. External ramp is needed when low-ESR capacitors, such as ceramic capacitors are used. For cases not listed in this datasheet, a calculator in excel spreadsheet can also be requested through a local sales representative to assist with the calculation.

-								
V _{OUT} (V)	L (µH)	R1 (kΩ)	R2 (kΩ)	R7 (kΩ)				
1.0	1.0	19.8	30	300				
1.2 1.	0	29.4	30	365				
1.5 1.	.0	29.4	20	453				
1.8 1.	0	39.2	20	549				
3.3 1.	.0	44.2	10	1000				

Table 2—C_{OUT}-Poscap, 600kHz, 5V_{IN}

Table 3—C_{OUT}-Poscap, 800kHz, 5VIN

-							
V _{out} (V)	L (µH)	R1 (kΩ)	R2 (kΩ)	R7 (kΩ)			
1.0	0.75	20	30	210			
1.2 0.	75	20	20	270			
1.5 0.	75	30	20	330			
1.8 0.	75	39	20	499			
3.3 0.	75	44.2	10	750			

Table 5—Cout-Ceramic, 600kHz, 5VIN VOUT L **R1 R2** R4 C4 **R7** (µH) (kΩ) (kΩ) (kΩ) (V) (pF) (kΩ) 1.0 21 1.0 30 240 470 309 1.2 1.0 33 30 220 470 365 1.5 1.0 51 30 330 390 464 1.8 1.0 45 20 270 470 549 3.3 1.0 62 10 160 680 953

Table 6—C_{out}-Ceramic, 800kHz, 5VIN

V _{out} (V)	L (µH)	R1 (kΩ)	R2 (kΩ)	R4 (kΩ)	C4 (pF)	R7 (kΩ)
1.0	0.75	21 30		200	470	226
1.2	0.75	34 30		200	470	270
1.5	0.75	34 20		220	470	324
1.8	0.75	47.5 2	D	225	470	402
3.3	0.75	57.6 1	D	200	560	750



TYPICAL APPLICATION

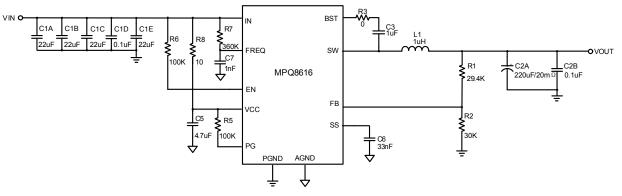


Figure 13 — Typical Application Circuit with No External Ramp

MPQ8616, V_{IN} =5V, V_{OUT} =1.2V, I_{OUT} =6/12A, f_{SW} =600kHz

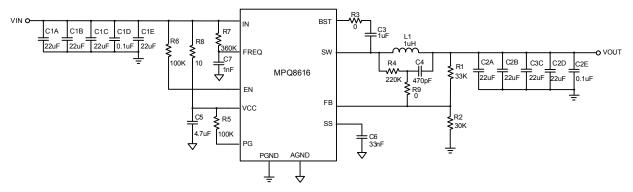


Figure 14 — Typical Application Circuit with Low ESR Ceramic Capacitor MPQ8616, V_{IN}=5V, V_{OUT}=1.2V, I_{OUT}=6/12A, f_{sw}=600kHz

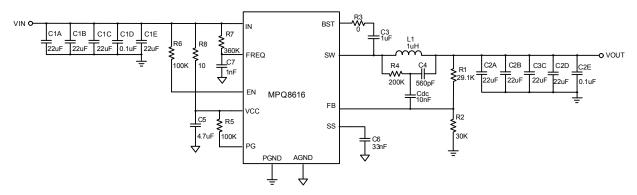
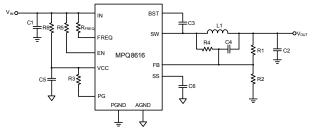


Figure 15 — Typical Application Circuit with Low ESR Ceramic Capacitor and DC-Blocking Capacitor. MPQ8616, V_{IN}=5V, V_{OUT}=1.2V, I_{OUT}=6/12A, f_{SW}=600kHz

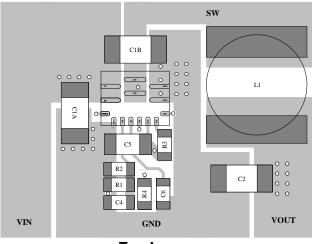


LAYOUT RECOMMENDATION

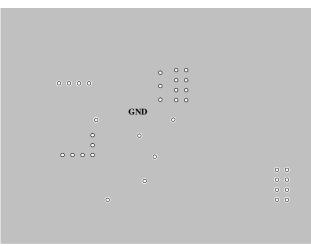
- 1. The high current paths (GND, IN, and SW) should be placed very close to t he device with short, direct and wide traces.
- 2. Put the input capacitor s as close to the I N and GND pins as possible.
- 3. Put the decoupling cap acitor as close to the VCC and GND pins as possible.
- 4. Keep the switching no de SW short and away from the feedback network.
- 5. The external feedback resistor s should be placed next to the FB pin. Make sure that there is no via on the FB trace.
- 6. Keep the B ST voltage path (BST, C3, and SW) as short as possible.
- 7. Keep the IN and GND pads conn ected with large copp er to achieve better thermal performance.
- 8. Four-layer layout is strongly recommended to achieve better thermal performance.



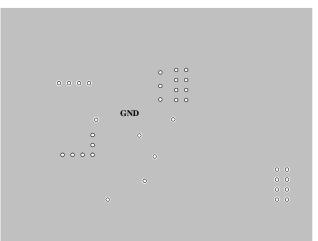
Schematic for PCB Layout Guide Line



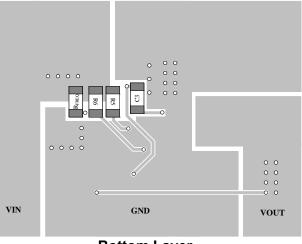
Top Layer



Inner1 Layer



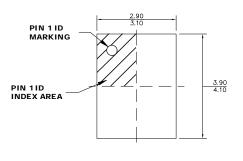
Inner2 Layer

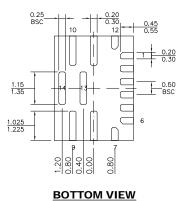


Bottom Layer Figure 16—PCB Layout



PACKAGE INFORMATION

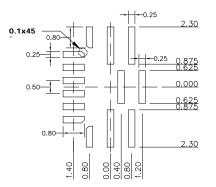




TOP VIEW



SIDE VIEW



<u>NOTE:</u>

 ALL DIMENSIONS ARE IN MILLIMETERS.
EXPOSED PADDLE SIZE DOES NOT INCLUDE MOLD FLASH
LEAD COPLANARITY SHALL BE0.10 MILLIMETERS MAX.
JEDEC REFERENCE IS MO-220.
DRAWING IS NOT TO SCALE.

RECOMMENDED LAND PATTERN

NOTICE: The information in this document is subject to change without notice. Please contact MPS for current specifications. Users should warrant and guarantee that third party Intellectual Property rights are not infringed upon when integrating MPS products into any application. MPS will not assume any legal responsibility for any said applications.